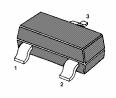
MMBTSC930

NPN Silicon Epitaxial Planar Transistor

for FM RF amp, mixer, osc, converter and IF amplifier.

The transistor is subdivided into four groups, C, D, E and F, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	30	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	-55 to +125	°C





MMBTSC930

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =6V, I _C =1mA						
Current Gain Group	С	h _{FE}	40	-	80	-
	D	h _{FE}	60	-	120	-
	Ε	h _{FE}	100	-	200	-
	F	h _{FE}	160	-	320	_
Collector Cutoff Current						
at V _{CB} =10V		I _{CBO}	-	-	1	μΑ
Emitter Cutoff Current						
at V _{EB} =4V		I _{EBO}	-	-	1	μA
Gain Bandwidth Product						
at V _{CE} =6V, I _C =1mA		f _T	170	300	-	MHz
Reverse Transfer Capacitance						
at V _{CB} =6V, f=1MHz		Cre	1	1.3	1.8	pF
Base to Collector Time Constant						
at V _{CB} =6V, I _C =1mA, f=31.9MHz		Rbb • Cc	-	20	36	ps
Noise Figure						
at V_{CB} =6V, I_{C} =1mA, f=100MHz		NF	-	4	-	dB
Turn-on Time						
at V _{IN} =+12V, V _{BE} =-3V,appointed circuit		t _{on}	-	30	-	ns
Turn-off Time						
at V_{IN} =-12V, V_{BE} =+3V, appointed circuit		t _{off}	-	30	-	ns





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